Elektronische Bauelemente

2SB1132

-1A, -40V

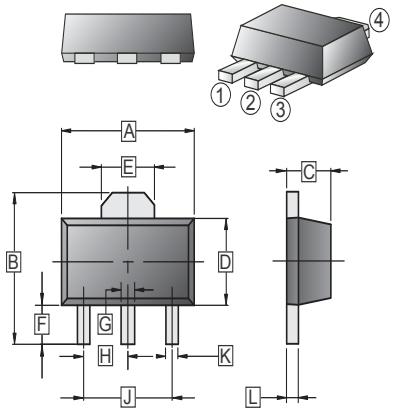
PNP Silicon Medium Power Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

- Low power dissipation 0.5W

SOT-89



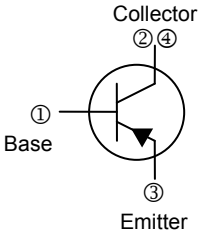
REF.	Millimeter Min.	Millimeter Max.	REF.	Millimeter Min.	Millimeter Max.
A	4.40	4.60	G	0.40	0.58
B	3.94	4.25	H	1.50	TYP
C	1.40	1.60	J	3.00	TYP
D	2.30	2.60	K	0.32	0.52
E	1.50	1.70	L	0.35	0.44
F	0.89	1.2			

CLASSIFICATION OF h_{FE}

Product Rank	2SB1132-P	2SB1132-Q	2SB1132-R
Range	82~180	120~270	180~390
Marking	BAP	BAQ	BAR

PACKAGE INFORMATION

Package	MPQ	Leader Size
SOT-89	1K	7' inch



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-32	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-1	A
Collector Power Dissipation	P_C	500	mW
Junction & Storage Temperature	T_J, T_{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-base breakdown voltage	$V_{(BR)CBO}$	-40	-	-	V	I_C= -50μA, I_E=0
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	-32	-	-	V	I_C= -1mA, I_B=0
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E= -50μA, I_C=0
Collector cut-off current	I_{CBO}	-	-	-0.5	μA	V_{CB}= -20V, I_E=0
Emitter cut-off current	I_{EBO}	-	-	-0.5	μA	V_{EB}= -4V, I_C=0
DC current gain	h_{FE}	82	-	390		V_{CE}= -3V, I_C= -100mA
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-0.2	-0.5	V	I_C= -500mA, I_B= -50mA
Transition frequency	f_T	-	150	-	MHz	V_{CE}= -5V, I_C= -50mA, f=30MHz
Collector output capacitance	C_{ob}	-	20	30	pF	V_{CB}= -10V, I_E=0, f=1MHz

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CHARACTERISTIC CURVES

